Alfa-MOS Technology

AFP7317WS
150V P-Channel Enhancement Mode MOSFET

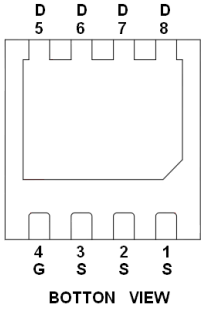
General Description

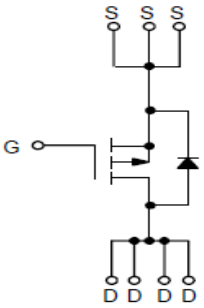
AFP7317WS, P-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.
These devices are particularly suited for low voltage power management, such as smart phone and notebook computer and other battery powered circuits, and low in-line power loss are needed in commercial industrial surface mount applications.

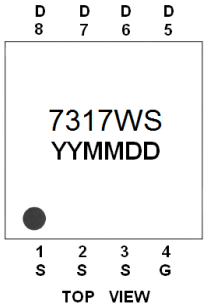
Features

- I_D=-1.4A,$R_{DS(ON)}$=750 mΩ@V_{GS}=-10V
- I_D=-1.0A,$R_{DS(ON)}$=800 mΩ@V_{GS}=-6V
- Super high density cell design for extremely low $R_{DS\ (ON)}$
- Exceptional on-resistance and maximum DC current capability
- DFN3X3-8L package design

Pin Description (DFN3X3-8L)







Application

- DC-DC Converter
- POL

Pin Define

Pin	Symbol	Description
1	S	Source
2	S	Source
3	S	Source
4	G	Gate
5	D	Drain
6	D	Drain
7	D	Drain
8	D	Drain

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFP7317WSFN338RG	7317WS	DFN3X3-8L	Tape & Reel	5000 EA

※ YY year code
※ MM month code
※ DD date code
※ AFP7317WSFN338RG : 13”Tape & Reel ; Pb- Free ; Halogen –Free

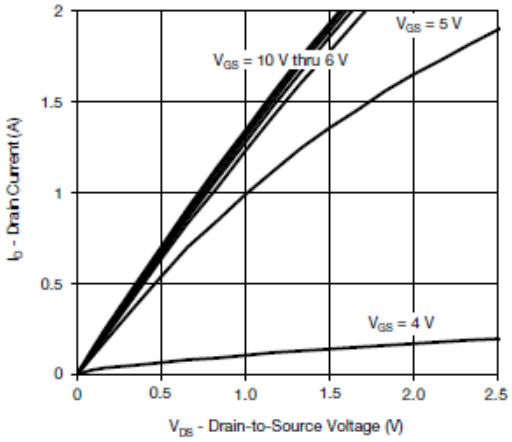
※ Absolute Maximum Ratings (T_A=25℃ Unless otherwise noted)

Parameter			Symbol	Value		Unit
Drain-Source Voltage			V_{DSS}	-150		V
Gate –Source Voltage			V_{GSS}	±20		V
Continuous Drain Current(T_J=150℃)	T_C=25℃	T_C=70℃	I_D	-3.0	-2.4	A
	T_A=25℃	T_A=70℃		-1.4	-1.0	
Pulsed Drain Current			I_{DM}	-3.2		A
Single pulse avalanche energy	L=1.0 mH		E_{AS}	0.5		mJ
Continuous Source Current (Diode Conduction)	T_C=25℃	T_A=25℃	I_S	-10	-2.7	A
Power Dissipation	T_C=25℃	T_C=70℃	P_D	28	15	W
	T_A=25℃	T_A=70℃		3.2	2.0	
Operating Junction Temperature			T_J	150		℃
Storage Temperature Range			T_{STG}	-55/150		℃
Thermal Resistance Junction-to-Case (Drain)			$R_{\theta JC}$	5		℃/W
Thermal Resistance-Junction to Ambient			$R_{\theta JA}$	40		

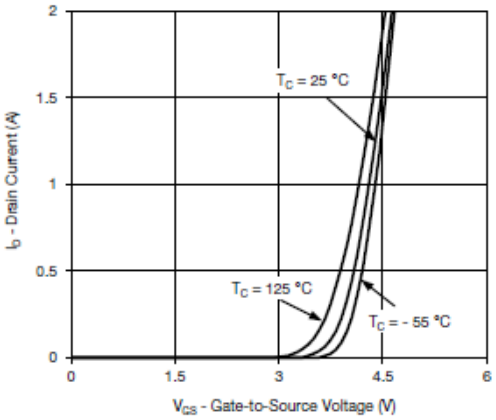
Electrical Characteristics (T_A=25℃ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=-250uA	-150			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250uA	-2.0		-4.0	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-120V,V_{GS}=0V			-1	uA
		V_{DS}=-120V,V_{GS}=0V T_J=85℃			-30	
On-State Drain Current	$I_{D(on)}$	V_{DS}≧-15V,V_{GS}=-10V	-1.6			A
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=-10V,I_D=-1.4A		685	750	mΩ
		V_{GS}=-6V,I_D=-1.0A		735	800	
Forward Transconductance	g_{FS}	V_{DS}=-15V,I_D=-0.5A		3		S
Diode Forward Voltage	V_{SD}	I_S=-1.0A,V_{GS}=0V		-0.75	-1.2	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=-75V,V_{GS}=-10V I_D≡-1.1A		7.0	12	nC
Gate-Source Charge	Q_{gs}			1.8		
Gate-Drain Charge	Q_{gd}			2.2		
Gate Resistance	R_g	f=1MHz		10	15	Ω
Pulse Diode Forward Current	I_{SM}				-12	A
Input Capacitance	C_{iss}	V_{DS}=-75V,V_{GS}=0V f=1MHz		280		pF
Output Capacitance	C_{oss}			20		
Reverse Transfer Capacitance	C_{rss}			15		
Turn-On Time	$t_{d(on)}$	V_{DD}=-75V,R_L=85Ω I_D≡-1.0A,V_{GEN}=-10V R_G=1.0Ω		10	20	ns
	t_r			15	30	
Turn-Off Time	$t_{d(off)}$			15	30	
	t_f			10	25	
Body Diode Reverse Recovery Time	t_{rr}	I_F=- 0.5 A, dI/dt=100 A/μs, T_J = 25 ℃		50	100	ns
Body Diode Reverse Recovery Charge	Q_{rr}			95	150	nC

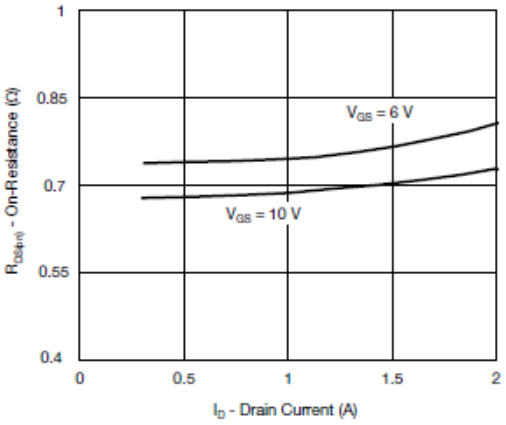
Typical Characteristics



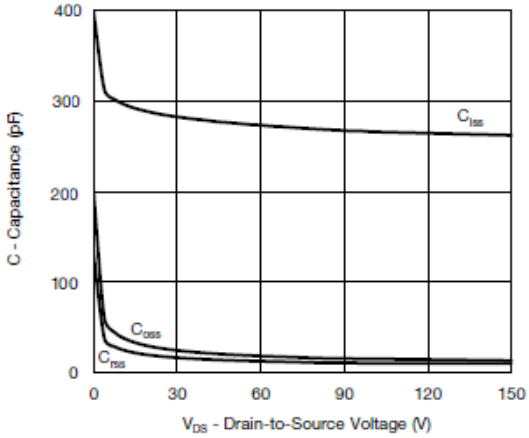
Output Characteristics



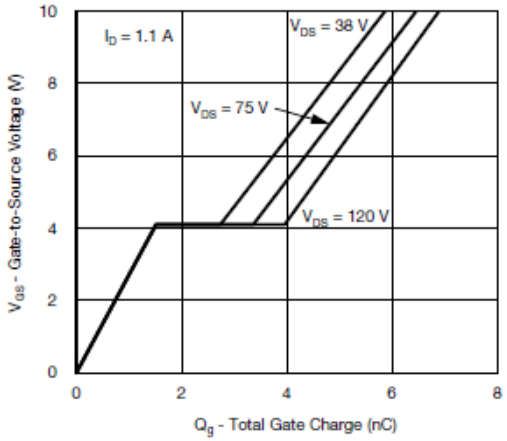
Transfer Characteristics



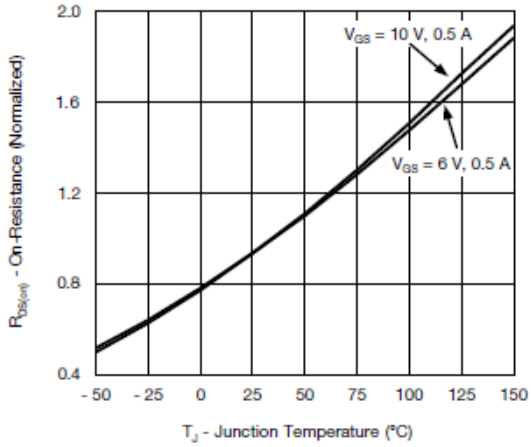
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

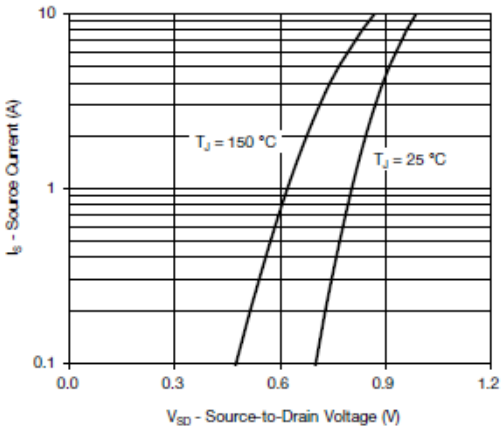


Gate Charge

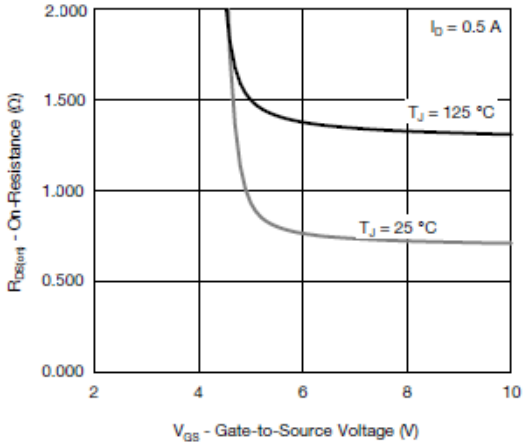


On-Resistance vs. Junction Temperature

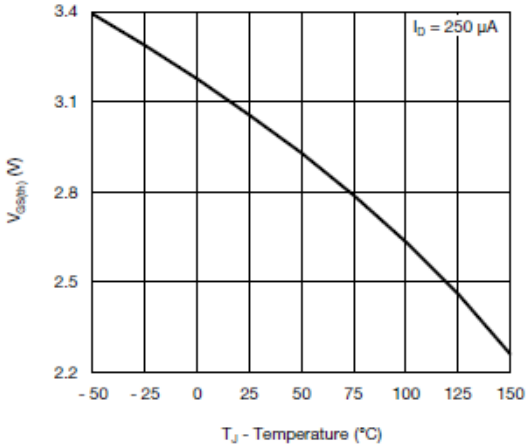
Typical Characteristics



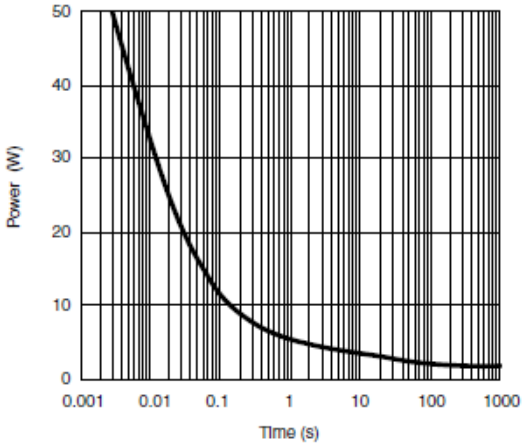
Source-Drain Diode Forward Voltage



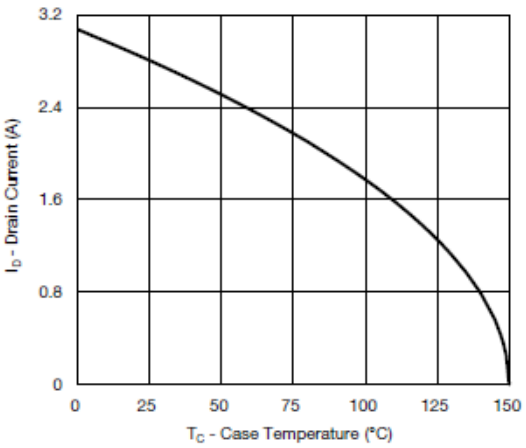
On-Resistance vs. Gate-to-Source Voltage



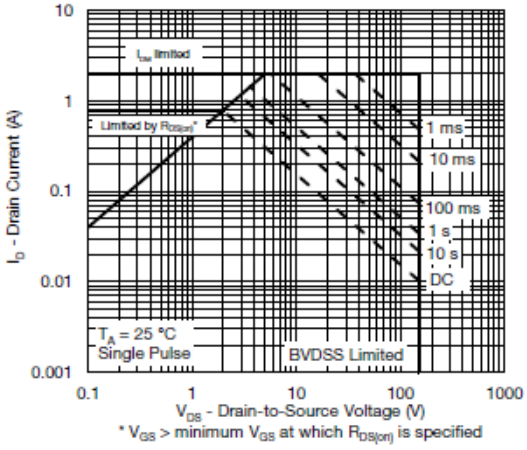
Threshold Voltage



Single Pulse Power, Junction-to-Ambient

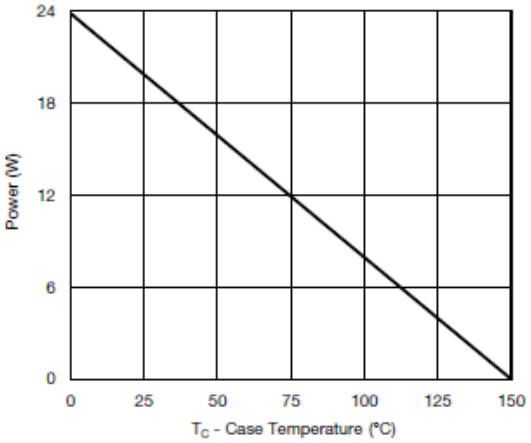


Max Current vs. Case Temperature

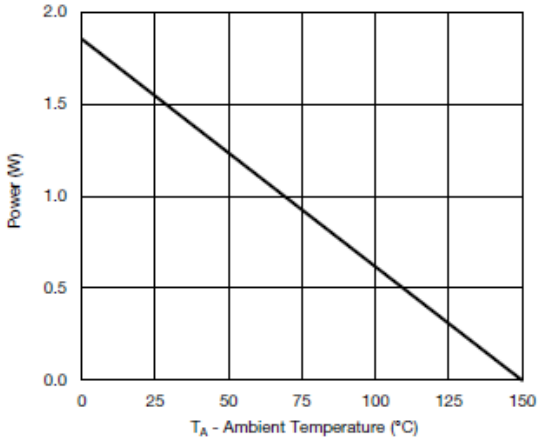


Safe Operating Area at T_A = 25 °C

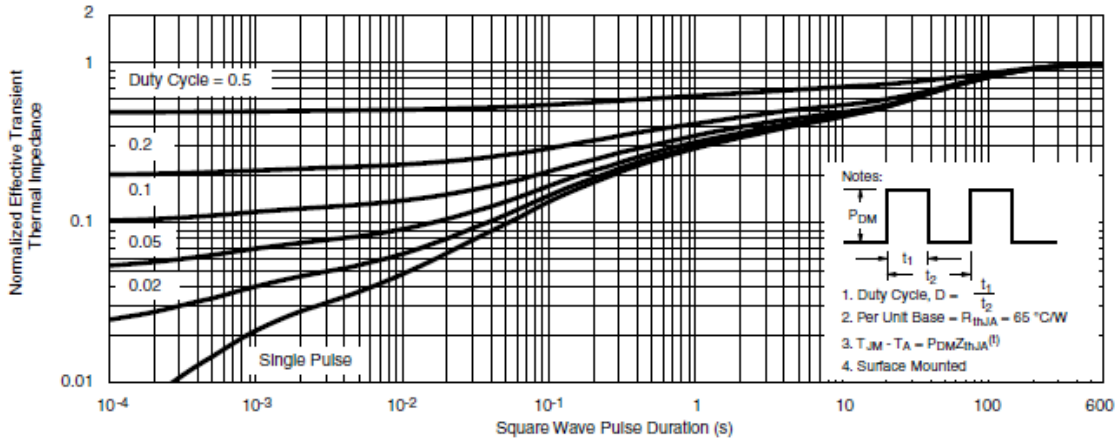
Typical Characteristics



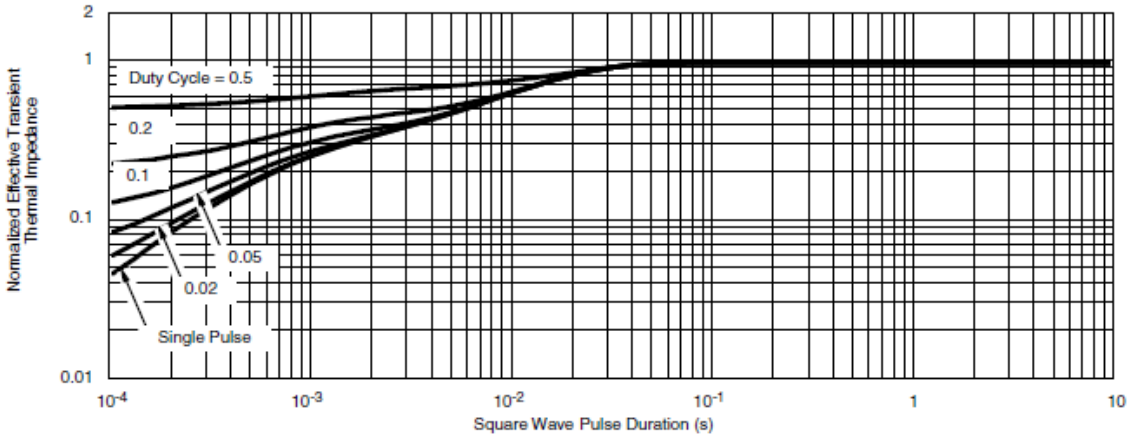
Power Junction-to-Case



Power Junction-to-Ambient



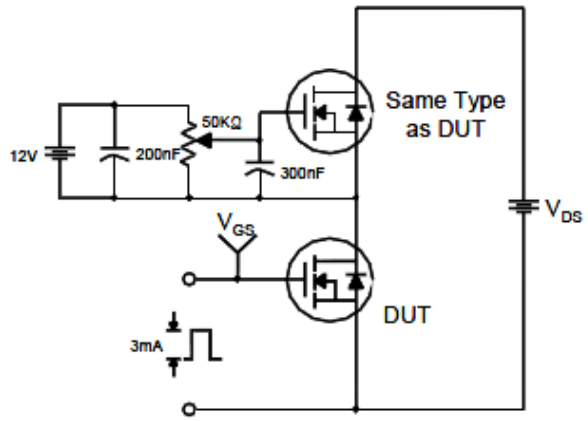
Normalized Thermal Transient Impedance, Junction-to-Ambient

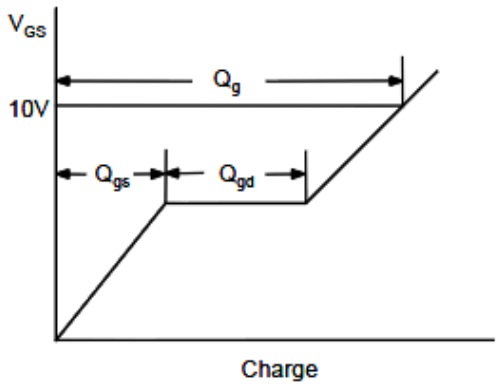


Normalized Thermal Transient Impedance, Junction-to-Case

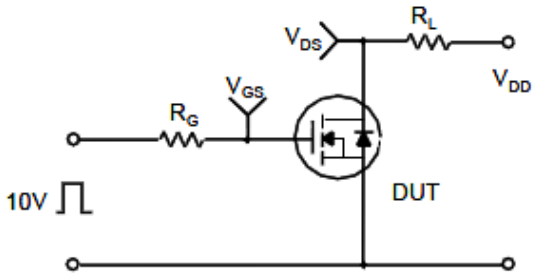
Typical Characteristics

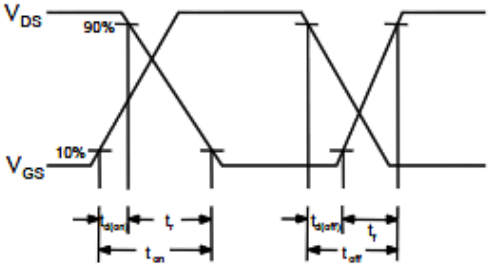
Gate Charge Test Circuit & Waveform



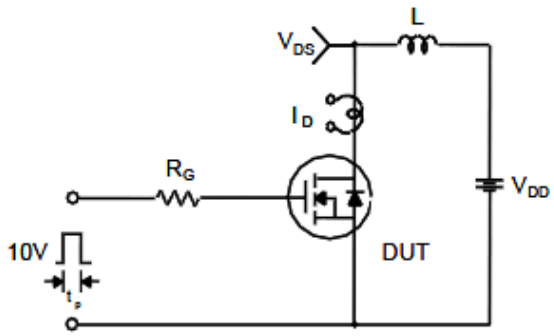


Resistive Switching Test Circuit & Waveforms

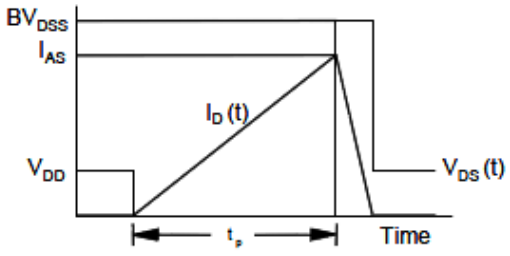




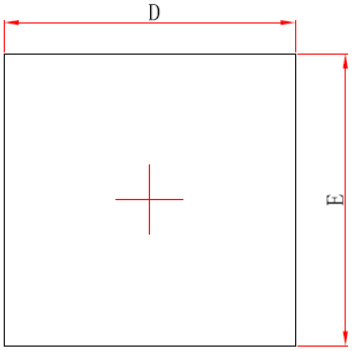
Unclamped Inductive Switching Test Circuit & Waveforms



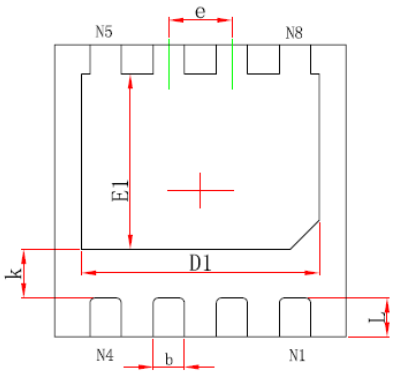
$$E_{AS} = \frac{1}{2} L I_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$



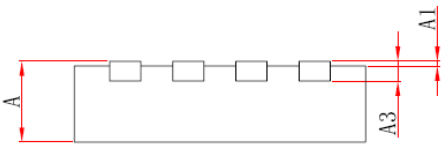
Package Information (DFN3X3-8L)



Top View



Bottom View



Side View

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	2.924	3.076	0.115	0.121
E	2.924	3.076	0.115	0.121
D1	2.350	2.550	0.093	0.100
E1	1.700	1.900	0.067	0.075
k	0.450	0.550	0.018	0.022
b	0.270	0.370	0.011	0.015
e	0.650TYP.		0.026TYP.	
L	0.324	0.476	0.013	0.019

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